

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1-72. (Cancelled)

73. (Previously Presented) An in-process device, comprising:

a substrate;

a conductive layer comprising a metal layer over the substrate, the conductive layer being exposed to a material selected from the group consisting of phosphine and methylsilane to reduce an ability of the conductive layer to associate with oxygen; and

a second conductive layer comprising a tungsten nitride layer formed on the conductive layer and a third conductive layer comprising a copper layer formed on the second conductive layer.

74. (Previously Presented) The in-process device of claim 73, wherein the conductive layer comprises tungsten nitride.

75. (Previously Presented) The device in claim 74, further comprising another conductive layer formed on the tungsten nitride layer.

76. (Cancelled)

77. (Previously Presented) The in-process device of claim 75 wherein the other conductive layer comprises copper.

78-79. (Cancelled)

80. (Previously Presented) The in-process device of claim 73 wherein the substrate comprises a silicon substrate.

81-94 (Cancelled)